

PMBTA45

500 V, 150 mA NPN high-voltage low V_{CEsat} (BISS) transistor

Rev. 02 — 10 March 2010 Product data she Product data sheet

Product profile 1.

1.1 General description

NPN high-voltage low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a SOT23 (TO-236AB) small Surface-Mounted Device (SMD) plastic package.

PNP complement: PBHV9050T.

1.2 Features and benefits

- High voltage
- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- AEC-Q101 qualified

1.3 Applications

- Electronic ballasts
- LED driver for LED chain module
- LCD backlighting
- Automotive motor management
- Flyback converters
- Hook switch for wired telecom
- Switch Mode Power Supply (SMPS)

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CESM}	collector-emitter peak voltage	$V_{BE} = 0 V$	-	-	500	V
V_{CEO}	collector-emitter voltage	open base	-	-	500	V
I _C	collector current		-	-	0.15	Α
h _{FE}	DC current gain	$V_{CE} = 10 \text{ V}; I_{C} = 30 \text{ mA}$	50	100	-	



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2. Pinning information

Table 2. Pinning

I dibio L.	9		
Pin	Description	Simplified outline	Graphic symbol
1	base		
2	emitter	3	3
3	collector	1 2	1 — 2
			svm021

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMBTA45	-	plastic surface-mounted package; 3 leads	SOT23

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
PMBTA45	LK*

- [1] * = -: made in Hong Kong
 - * = p: made in Hong Kong
 - * = t: made in Malaysia
 - * = W: made in China

5. Limiting values

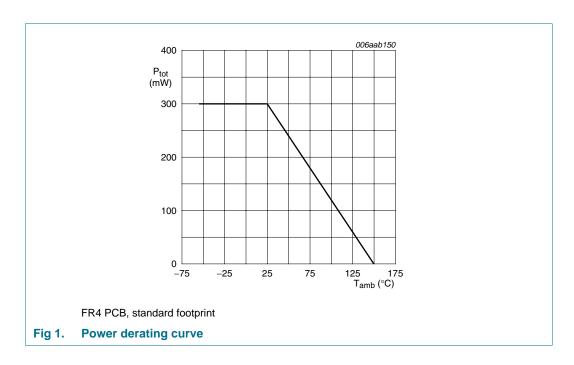
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		• • •	-		
Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	500	V
V_{CEO}	collector-emitter voltage	open base	-	500	V
V_{CESM}	collector-emitter peak voltage	$V_{BE} = 0 V$	-	500	V
V_{EBO}	emitter-base voltage	open collector	-	6	V
I _C	collector current		-	0.15	Α
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	0.5	Α
I _{BM}	peak base current	single pulse; $t_p \le 1 \text{ ms}$	-	200	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	<u>[1]</u> _	300	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-55	+150	°C
T _{stg}	storage temperature		-65	+150	°C
•	The state of the s				· ·

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^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



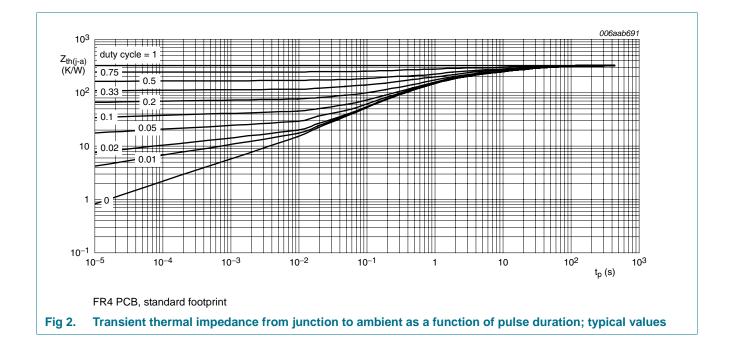
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6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u>	-	-	417	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	70	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



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7. Characteristics

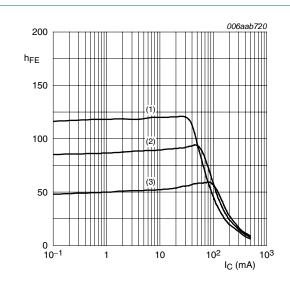
Table 7. Characteristics

 $T_{amb} = 25$ °C unless otherwise specified.

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I _{CBO}		$V_{CB} = 360 \text{ V}; I_E = 0 \text{ A}$		-	-	100	nA
current	current	$V_{CB} = 360 \text{ V}; I_E = 0 \text{ A};$ $T_j = 150 \text{ °C}$		-	-	10	μΑ
I _{CES}	collector-emitter cut-off current	$V_{CE} = 360 \text{ V}; V_{BE} = 0 \text{ V}$		-	-	100	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$		-	-	100	nA
h _{FE}	DC current gain	V _{CE} = 10 V					
		$I_C = 30 \text{ mA}$		50	100	-	
		I _C = 50 mA	[1]	50	100	-	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 20 \text{ mA}; I_B = 2 \text{ mA}$		-	60	75	mV
sat		$I_C = 50 \text{ mA}; I_B = 6 \text{ mA}$	[1]	-	65	90	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = 50 \text{ mA}; I_B = 5 \text{ mA}$	[1]	-	0.75	0.9	V
f _T	transition frequency	$V_{CE} = 10 \text{ V}; I_{E} = 10 \text{ mA};$ f = 100 MHz		-	35	-	MHz
C _c	collector capacitance	$V_{CB} = 20 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz		-	4	-	pF
C _e	emitter capacitance	$V_{EB} = 0.5 \text{ V};$ $I_{C} = i_{c} = 0 \text{ A}; f = 1 \text{ MHz}$		-	200	-	pF
t _d	delay time	$V_{CC} = 20 \text{ V}; I_C = 0.05 \text{ A};$		-	80	-	ns
t _r	rise time	「l _{Bon} = 5 mA; - l _{Boff} = −10 mA		-	2700	-	ns
t _{on}	turn-on time	IBoff = -IUIIIA		-	2780	-	ns
t _s	storage time			-	3400	-	ns
t _f	fall time			-	800	-	ns
t _{off}	turn-off time			-	4200	-	ns

^[1] Pulse test: $t_p \leq 300~\mu s;~\delta \leq 0.02.$

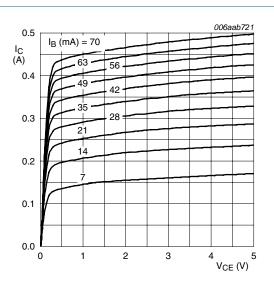
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$$V_{CE} = 10 \text{ V}$$

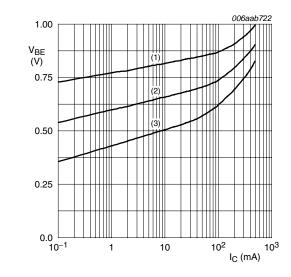
- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -55 \, ^{\circ}C$

Fig 3. DC current gain as a function of collector current; typical values



 $T_{amb} = 25 \, ^{\circ}C$

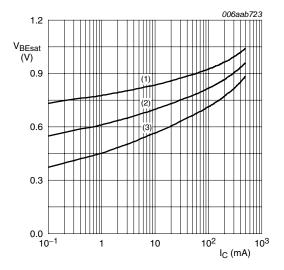
Fig 4. Collector current as a function of collector-emitter voltage; typical values





- (1) $T_{amb} = -55 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 100 \, ^{\circ}C$

Fig 5. Base-emitter voltage as a function of collector current; typical values

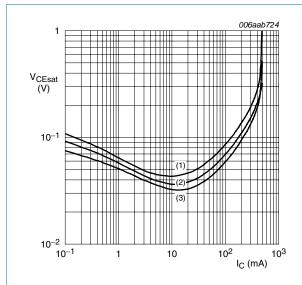


 $I_{\rm C}/I_{\rm B}=5$

- (1) $T_{amb} = -55 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 100 \, ^{\circ}C$

Fig 6. Base-emitter saturation voltage as a function of collector current; typical values

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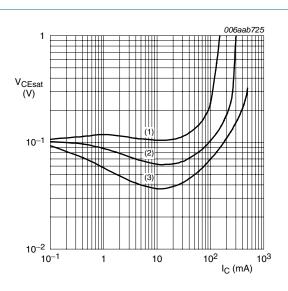
$$I_{\rm C}/I_{\rm B}=5$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig 7. Collector-emitter saturation voltage as a function of collector current; typical values



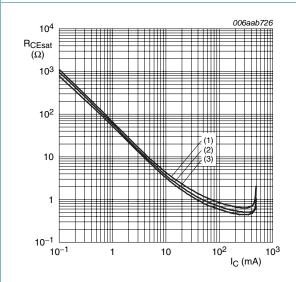
$$T_{amb} = 25 \, ^{\circ}C$$

(1)
$$I_C/I_B = 20$$

(2)
$$I_C/I_B = 10$$

(3) $I_C/I_B = 5$

Fig 8. Collector-emitter saturation voltage as a function of collector current; typical values



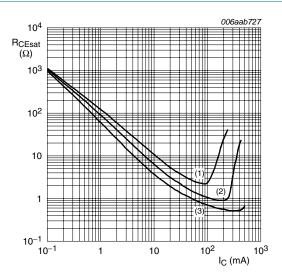
$$I_{\rm C}/I_{\rm B}=5$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 9. Collector-emitter saturation resistance as a function of collector current; typical values



(1)
$$I_C/I_B = 20$$

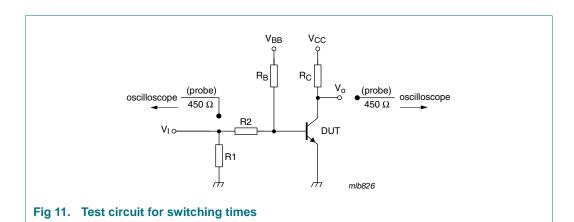
(2)
$$I_C/I_B = 10$$

(3)
$$I_C/I_B = 5$$

Fig 10. Collector-emitter saturation resistance as a function of collector current; typical values

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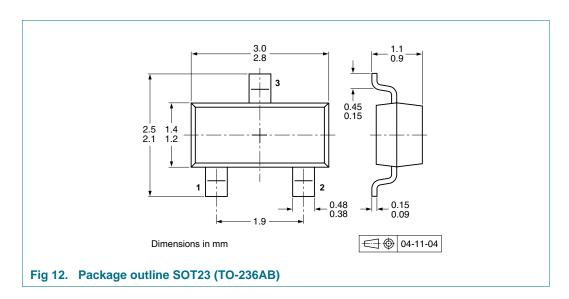
8. Test information



8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



10. Packing information

Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity	
			3000	10000
PMBTA45	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235

^[1] For further information and the availability of packing methods, see Section 14.

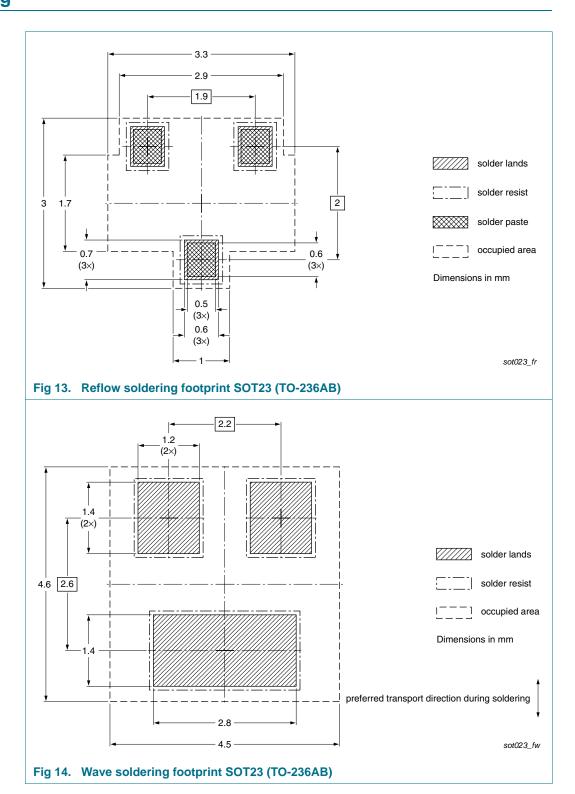
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11. Soldering



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12. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMBTA45_2	20100310	Product data sheet	-	PMBTA45_1
Modifications:	• Figure 7: up	dated		
PMBTA45_1	20090916	Product data sheet	-	-

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13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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